深圳市翔芯微科技有限公司

Shenzhen City Cheung core Micro Technology Co., Ltd.



BTA312 series B and C

12 A Three-quadrant triacs high commutation Rev. 01 — 13 March 2007

Product data sheet

Product profile

1.1 General description

Passivated, new generation, high commutation triacs, in a SOT78 plastic package.

1.2 Features

- Very high commutation performance maximized at each gate sensitivity
- High immunity to dV/dt

1.3 Applications

- High power motor control e.g. washing machines, vacuum cleaners
- Refrigeration and air conditioning compressors
- Non-linear rectifier-fed motor loads
- Electronic thermostats

1.4 Quick reference data

- $V_{DRM} \le 600 \text{ V (BTA312-600B/C)}$
- $V_{DRM} \le 800 \text{ V (BTA312-800B/C)}$
- $I_{TSM} \le 95 \text{ A (t = 20 ms)}$
- $I_{GT} \le 50 \text{ mA (BTA312 series B)}$
- $I_{GT} \le 35 \text{ mA (BTA312 series C)}$
- $I_{T(RMS)} \leq 12 A$

Pinning information 2.

Table 1. **Pinning**

Pin	Description	Simplified outline	Symbol
1	main terminal 1 (T1)		
2	main terminal 2 (T2)	mb	T2—T1
3	gate (G)	7 0 5	`G sym051
mb	mounting base; main terminal 2 (T2)		
		SOT78 (TO-220AB)	



3. Ordering information

Table 2. Ordering information

Type number	Package					
	Name	Description	Version			
BTA312-600B	SC-46	plastic single-ended package; heatsink mounted; 1 mounting hole;	SOT78			
BTA312-600C		3-lead TO-220AB				
BTA312-800B						
BTA312-800C						

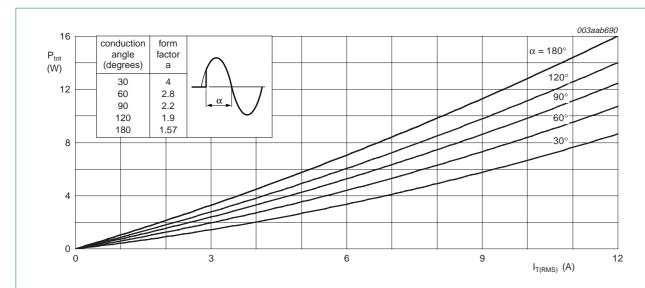
4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

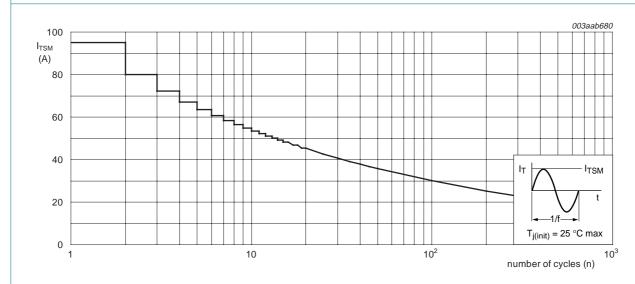
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage	BTA312-600B; BTA312-600C	<u>[1]</u> -	600	V
		BTA312-800B; BTA312-800C	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 101$ °C; see Figure 4 and 5	-	12	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3			
		t = 20 ms	-	95	Α
		t = 16.7 ms	-	105	Α
l ² t	I ² t for fusing	t = 10 ms	-	45	A ² s
dI _T /dt	rate of rise of on-state current	$I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-	100	A/μs
I_{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	125	°C

^[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.



 α = conduction angle

Fig 1. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

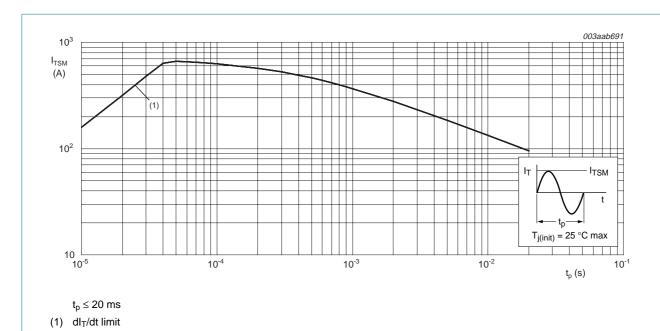


Fig 3. Non-repetitive peak on-state current as a function of pulse duration; maximum values

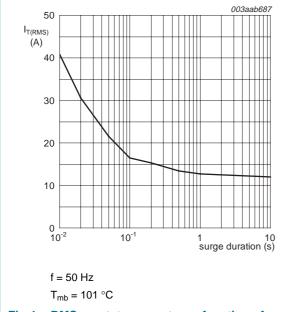


Fig 4. RMS on-state current as a function of surge duration; maximum values

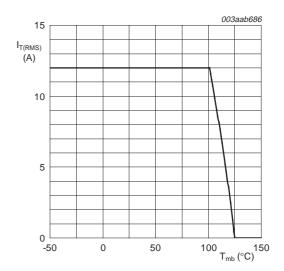
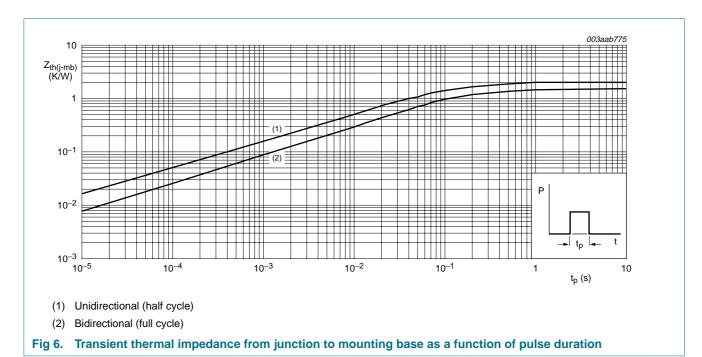


Fig 5. RMS on-state current as a function of mounting base temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	half cycle; see Figure 6	-	-	2.0	K/W
		full cycle; see Figure 6	-	-	1.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



6. Static characteristics

Table 5. Static characteristics

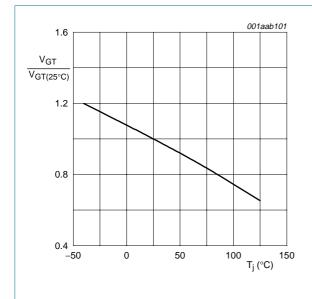
 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

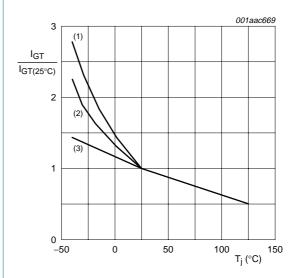
Symbol	Parameter	Conditions		BTA312-600B BTA312-800B			BTA312-600C BTA312-800C		
				Тур	Max	Min	Тур	Max	
I_{GT}	gate trigger	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; see } \frac{\text{Figure 8}}{}$							
	current	T2+ G+	2	-	50	2	-	35	mΑ
		T2+ G-	2	-	50	2	-	35	mΑ
		T2- G-	2	-	50	2	-	35	mΑ
IL	latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}; \text{ see } \frac{\text{Figure } 10}{}$							
		T2+ G+	-	-	60	-	-	50	mΑ
		T2+ G-	-	-	90	-	-	60	mΑ
		T2- G-	-	-	60	-	-	50	mΑ
I _H	holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}; \text{ see } \frac{\text{Figure } 11}{}$	-	-	60	-	-	35	mΑ
V_{T}	on-state voltage	I _T = 15 A; see <u>Figure 9</u>	-	1.3	1.6	-	1.3	1.6	V
V_{GT}	gate trigger	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ see } \frac{\text{Figure 7}}{}$	-	0.8	1.5	-	0.8	1.5	V
	voltage	$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C}$	0.25	0.4	-	0.25	0.4	-	V
I _D	off-state current	$V_D = V_{DRM(max)}$; $T_j = 125 ^{\circ}C$	-	0.1	0.5	-	0.1	0.5	mΑ

7. Dynamic characteristics

Table 6. Dynamic characteristics

Symbol	Parameter	Conditions	BTA312-600B BTA312-800B			BTA312-600C BTA312-800C			Unit
				Тур	Max	Min	Тур	Max	
dV _D /dt	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)}$; $T_j = 125$ °C; exponential waveform; gate open circuit	1000	2000	-	500	-	-	V/μs
dI _{com} /dt	rate of change of commutating current	$V_{DM} = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 12 \text{ A};$ without snubber; gate open circuit	30	-	-	20	-	-	A/ms
t _{gt}	gate-controlled turn-on time	I_{TM} = 20 A; V_D = $V_{DRM(max)}$; I_G = 0.1 A; dI_G/dt = 5 A/ μs	-	2	-	-	2	-	μs



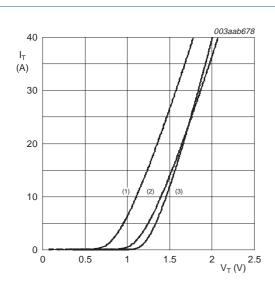


- (1) T2-G-
- (2) T2+ G-
- (3) T2+ G+

Fig 7. Normalized gate trigger voltage as a function of junction temperature

Fig 8. Normalized gate trigger current as a function of junction temperature

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 $V_0 = 1.127 V$

 $R_s = 0.027 \Omega$

- (1) $T_j = 125 \,^{\circ}\text{C}$; typical values
- (2) T_i = 125 °C; maximum values
- (3) $T_i = 25$ °C; maximum values

Fig 9. On-state current as a function of on-state voltage

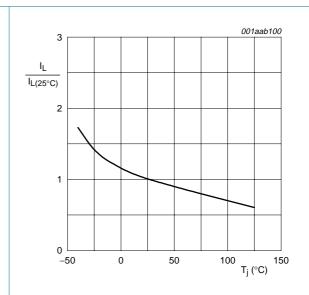


Fig 10. Normalized latching current as a function of junction temperature

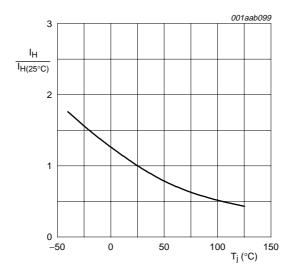


Fig 11. Normalized holding current as a function of junction temperature

8. Package outline

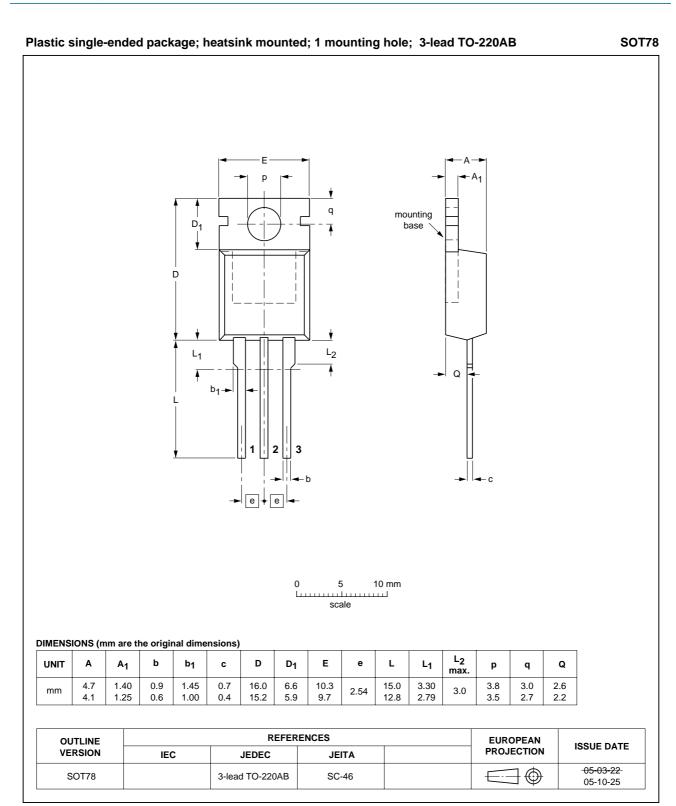


Fig 12. Package outline SOT78 (3-lead TO-220AB)

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9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA312_SER_B_C_1	20070313	Product data sheet	-	-

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10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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